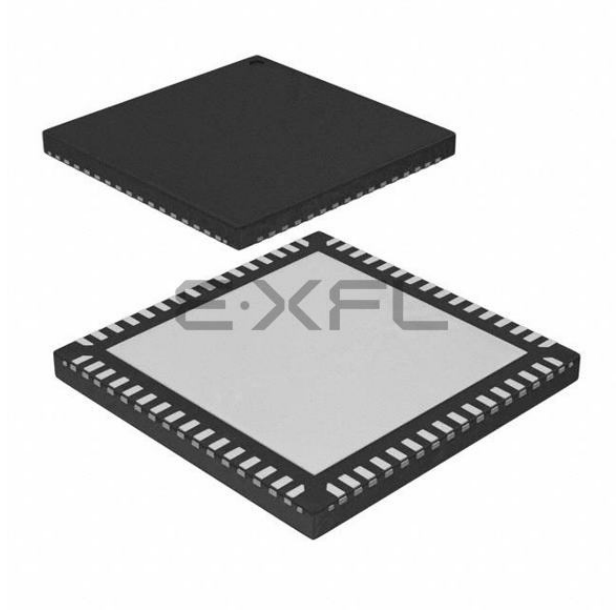
Silicon Labs - EFM32TG840F16-QFN64T Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	56
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg840f16-qfn64t

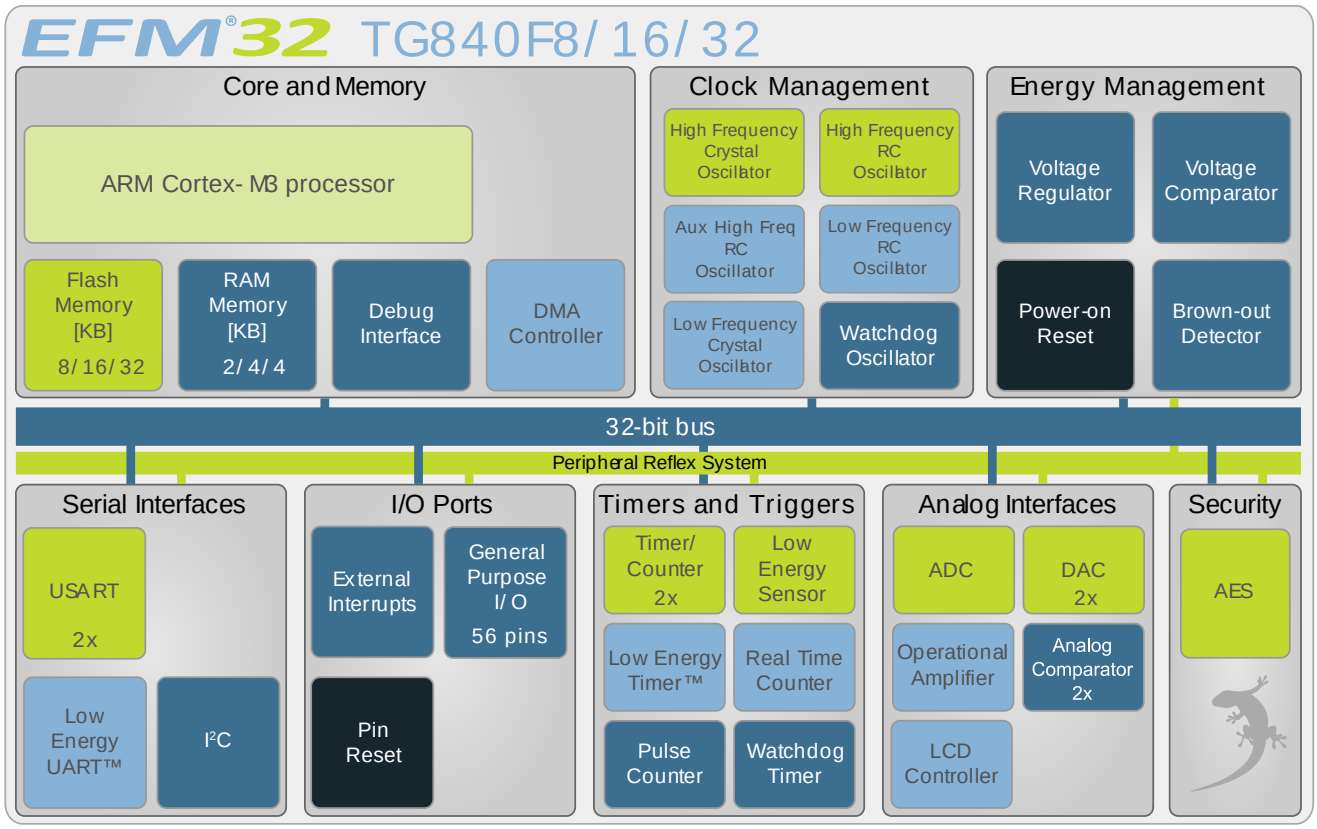
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32TG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32TG840 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32TG Reference Manual*.

A block diagram of the EFM32TG840 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep is included as well. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32 Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface . In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.3 Memory System Controller (MSC)

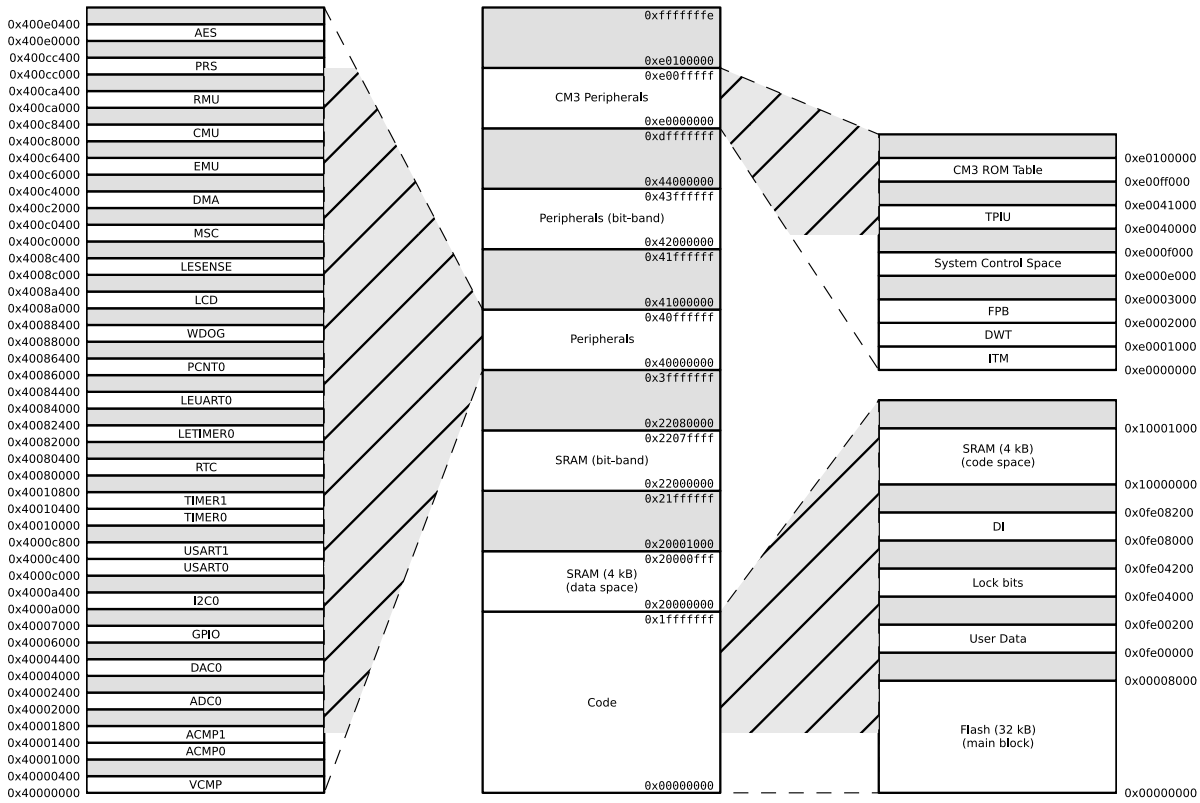
The Memory System Controller (MSC) is the program memory unit of the EFM32TG microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is

Module	Configuration	Pin Connections
GPIO	56 pins	Available pins are shown in Table 4.3 (p. 53)
LCD	Full configuration	LCD_SEG[19:0], LCD_COM[7:0], LCD_BCAP_P, LCD_BCAP_N, LCD_BEXT

2.3 Memory Map

The *EFM32TG840* memory map is shown in Figure 2.2 (p. 8), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32TG840 Memory Map with largest RAM and Flash sizes



3.4 Current Consumption

Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{EM0}	EM0 current. No prescaling. Running prime number calculation code from Flash. (Production test condition = 14 MHz)	32 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		157		µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		150	170	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		153	172	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		155	175	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		157	178	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		162	183	µA/MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		200	240	µA/MHz
I_{EM1}	EM1 current (Production test condition = 14 MHz)	32 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		53		µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		51	57	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		55	59	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		56	61	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		58	63	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		63	68	µA/MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V		100	122	µA/MHz
I_{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=25°C		1.0	1.2	µA
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		2.4	5.0	µA
I_{EM3}	EM3 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.59	1.0	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		2.0	4.5	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.055	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.25	0.70	µA

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{P_ERASE}	Page erase time		20	20.4	20.8	ms
t_{D_ERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

[1]Measured at 25°C

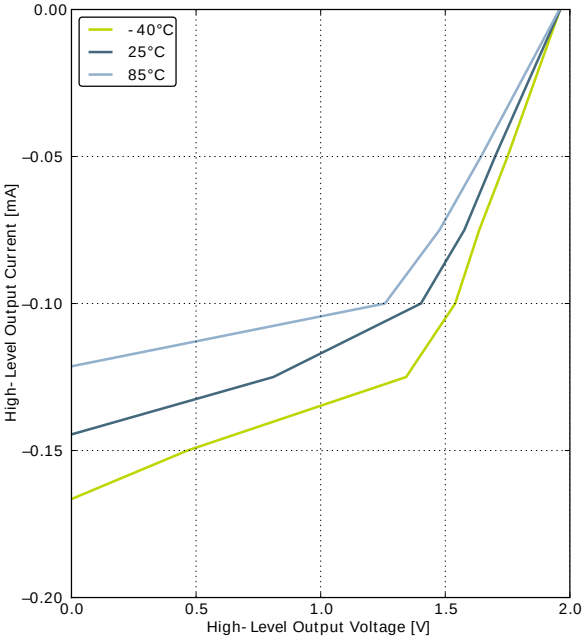
3.8 General Purpose Input Output

Table 3.7. GPIO

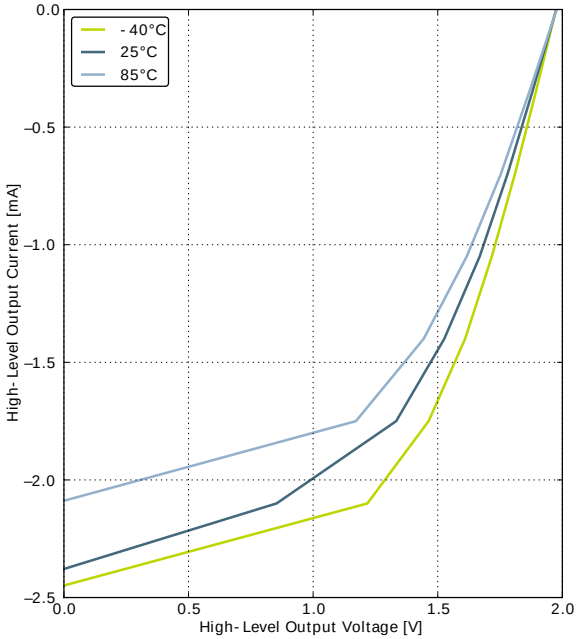
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V_{DD}			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V_{DD}		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V_{DD}		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V_{DD}	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V_{DD}	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V_{DD}	V
		Sinking 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.20V_{DD}	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or V_{DD}		±0.1	±100	nA
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance C_L=12.5-25pF.	20+0.1C_L		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C_L=350-600pF	20+0.1C_L		250	ns
V_{IOHYST}	I/O pin hysteresis (V_{IOTHR+} - V_{IOTHR-})	V_{DD} = 1.98 - 3.8 V	0.1V_{DD}			V

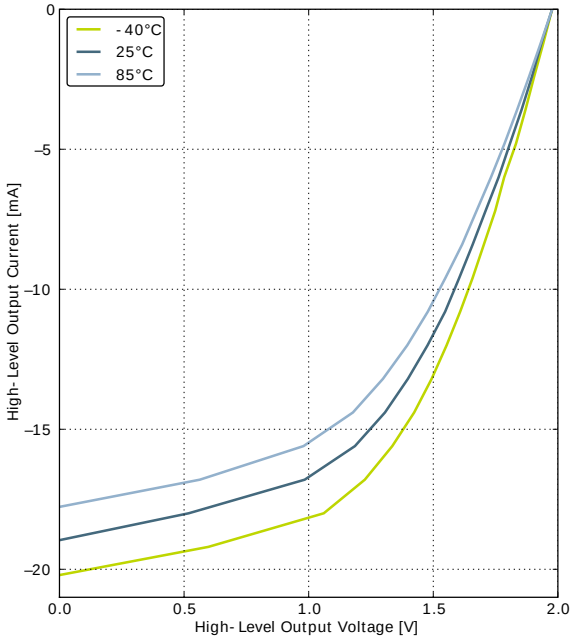
Figure 3.5. Typical High-Level Output Current, 2V Supply Voltage



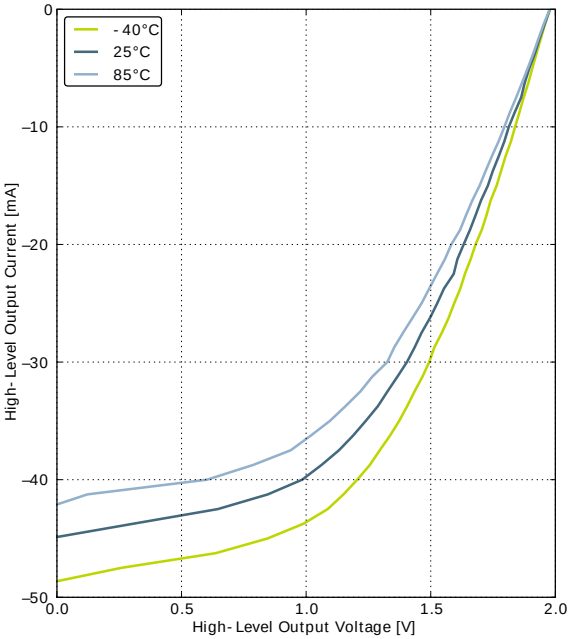
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

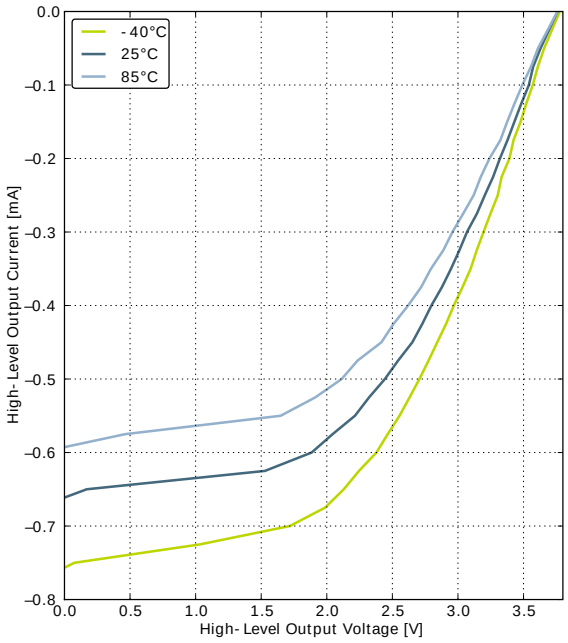


GPIO_Px_CTRL DRIVEMODE = STANDARD

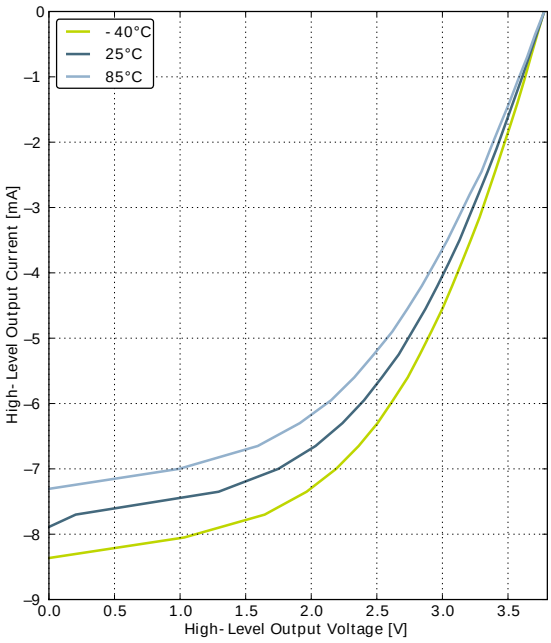


GPIO_Px_CTRL DRIVEMODE = HIGH

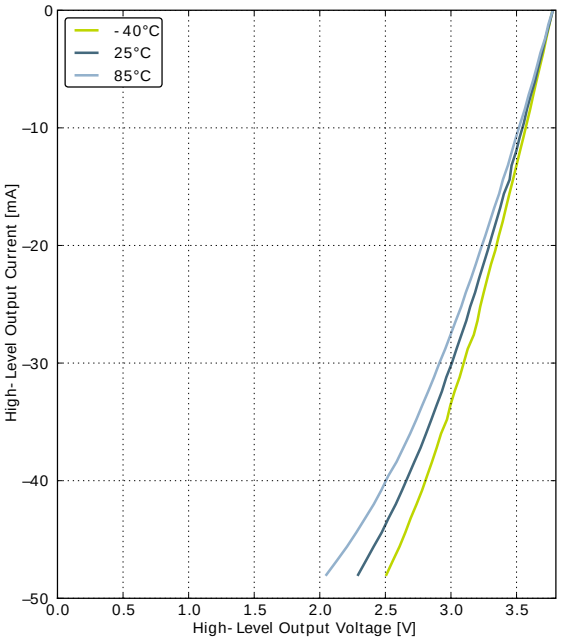
Figure 3.9. Typical High-Level Output Current, 3.8V Supply Voltage



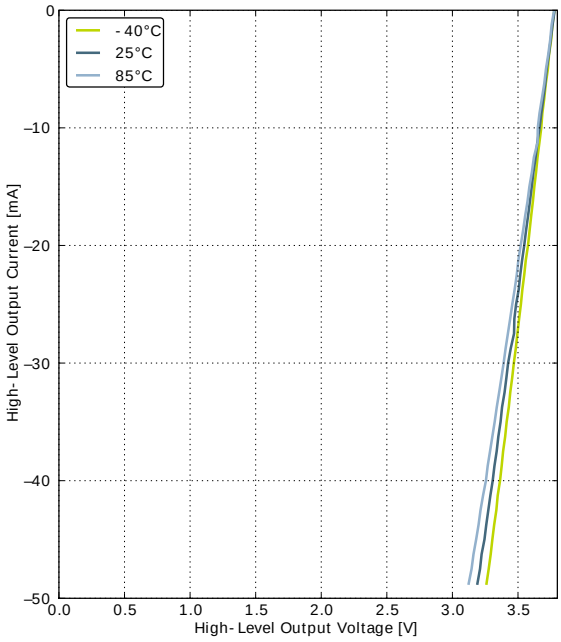
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.13. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

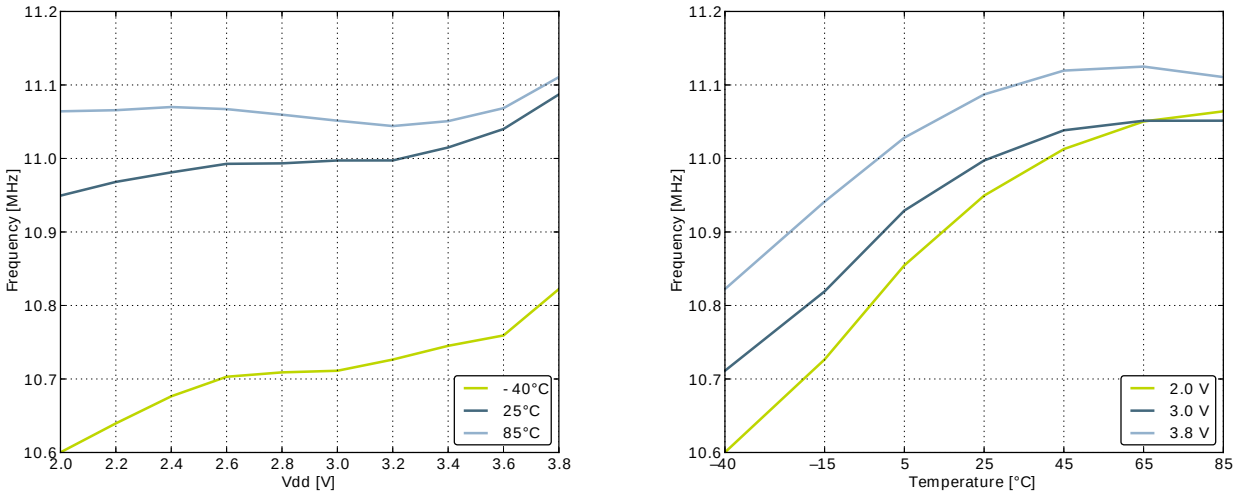


Figure 3.14. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature

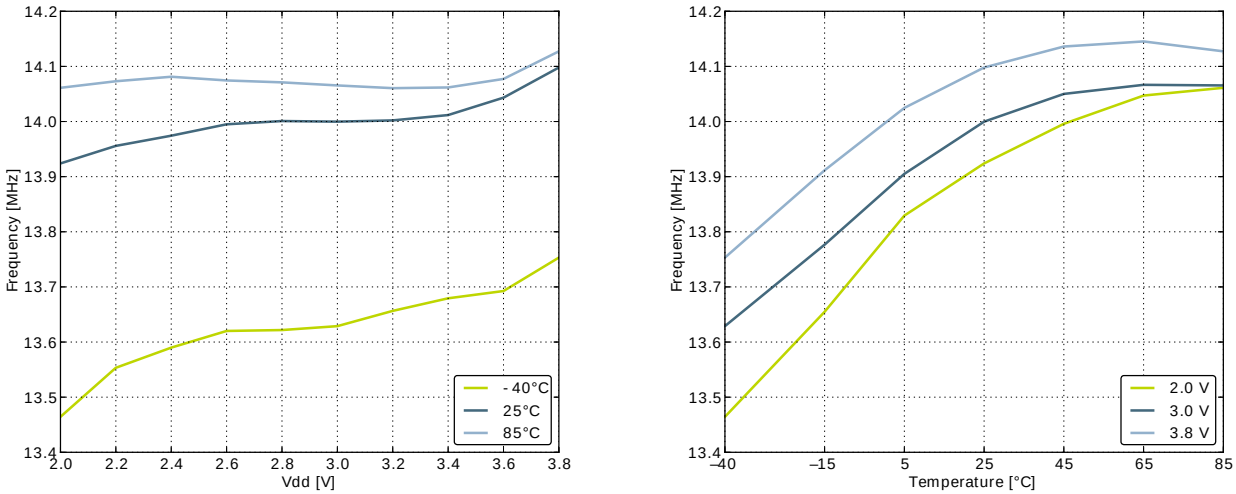
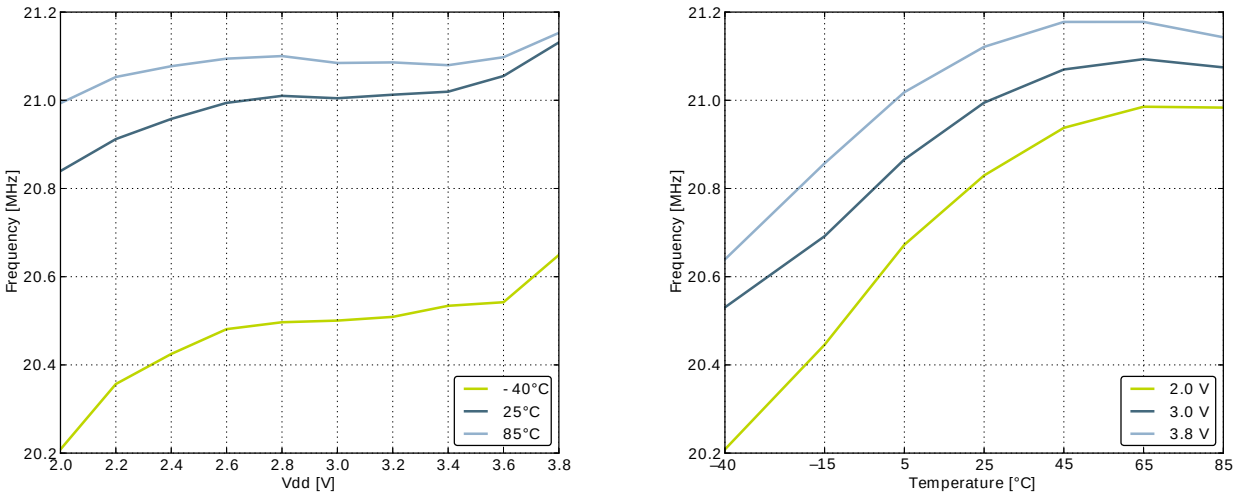


Figure 3.15. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature



Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ADCCLK}	ADC Clock Frequency				13	MHz
$t_{ADCCONV}$	Conversion time	6 bit	7			ADCCLK Cycles
		8 bit	11			ADCCLK Cycles
		12 bit	13			ADCCLK Cycles
t_{ADCACQ}	Acquisition time	Programmable	1		256	ADCCLK Cycles
$t_{ADCACQVDD3}$	Required acquisition time for VDD/3 reference		2			µs
$t_{ADCSTART}$	Startup time of reference generator and ADC core in NORMAL mode			5		µs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		µs
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference	63	67		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		OPAxHCMDIS=1	V_{SS}		V_{DD}-1.2	V
V_{OUTPUT}	Output Voltage		V_{SS}		V_{DD}	V
V_{OFFSET}	Input Offset Voltage	Unity Gain, V_{SS}<V_{in}<V_{DD}, OPAxHCMDIS=0		6		mV
		Unity Gain, V_{SS}<V_{in}<V_{DD}-1.2, OPAxHCMDIS=1		1		mV
V_{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR_{OPAMP}	Slew Rate	OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		46.11		V/µs
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.21		V/µs
		OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/µs
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		4.43		V/µs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		1.30		V/µs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/µs
PU_{OPAMP}	Power-up Time	OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		0.09		µs
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.52		µs
		OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		12.74		µs
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		0.09		µs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		0.13		µs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.17		µs
N_{OPAMP}	Voltage Noise	V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=0		101		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=1		141		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		196		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		1630		μV_{RMS}

Figure 3.26. OPAMP Negative Power Supply Rejection Ratio

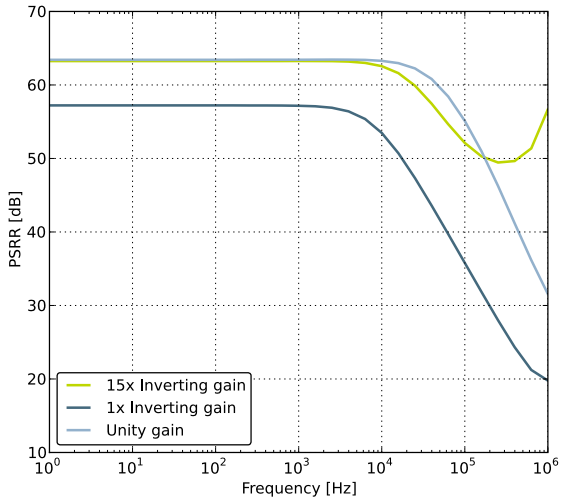


Figure 3.27. OPAMP Voltage Noise Spectral Density (Unity Gain) V_{out}=1V

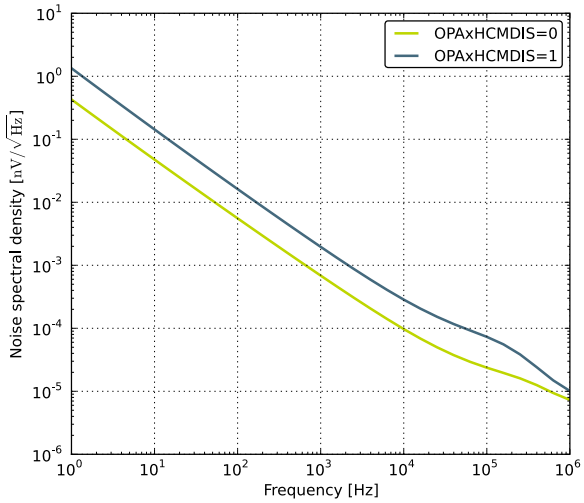
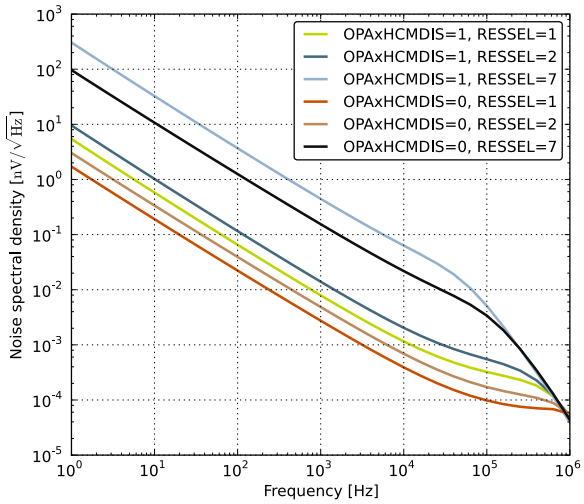


Figure 3.28. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)



3.16 I2C

Table 3.20. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100[1]	kHz
t_{LOW}	SCL clock low time	4.7			µs
t_{HIGH}	SCL clock high time	4.0			µs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			µs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			µs
$t_{SU,STO}$	STOP condition set-up time	4.0			µs
t_{BUF}	Bus free time between a STOP and START condition	4.7			µs

[1]For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32TG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < (($3450*10^{-9}$ [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.21. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and START condition	1.3			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32TG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < (($900*10^{-9}$ [s] * $f_{HFPERCLK}$ [Hz]) - 4).

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32TG840.

4.1 Pinout

The *EFM32TG840* pinout is shown in Figure 4.1 (p. 46) and Table 4.1 (p. 46). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32TG840 Pinout (top view, not to scale)

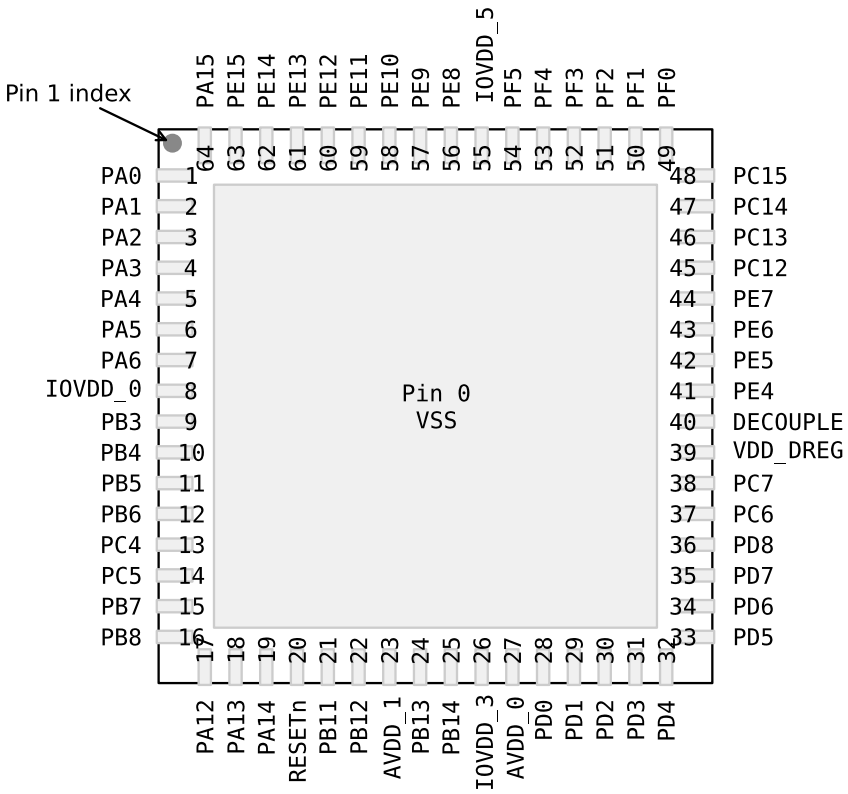


Table 4.1. Device Pinout

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
0	VSS	Ground.			
1	PA0	LCD_SEG13	TIM0_CC0 #0/1/4	LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 GPIO_EM4WU0
2	PA1	LCD_SEG14	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
		OPAMP_N2			
32	PD4	ADC0_CH4 OPAMP_P2		LEU0_TX #0	
33	PD5	ADC0_CH5 OPAMP_OUT2 #0		LEU0_RX #0	
34	PD6	ADC0_CH6 DAC0_P1 / OPAMP_P1	TIM1_CC0 #4 LETIM0_OUT0 #0 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2
35	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1	TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2
36	PD8				CMU_CLK1 #1
37	PC6	ACMP0_CH6		I2C0_SDA #2	LES_CH6 #0
38	PC7	ACMP0_CH7		I2C0_SCL #2	LES_CH7 #0
39	VDD_DREG	Power supply for on-chip voltage regulator.			
40	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size $C_{DECOUPLE}$ is required at this pin.			
41	PE4	LCD_COM0		US0_CS #1	
42	PE5	LCD_COM1		US0_CLK #1	
43	PE6	LCD_COM2		US0_RX #1	
44	PE7	LCD_COM3		US0_TX #1	
45	PC12	ACMP1_CH4 DAC0_OUT1ALT #0/ OPAMP_OUT1ALT			CMU_CLK0 #1 LES_CH12 #0
46	PC13	ACMP1_CH5 DAC0_OUT1ALT #1/ OPAMP_OUT1ALT	TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0		LES_CH13 #0
47	PC14	ACMP1_CH6 DAC0_OUT1ALT #2/ OPAMP_OUT1ALT	TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3	LES_CH14 #0
48	PC15	ACMP1_CH7 DAC0_OUT1ALT #3/ OPAMP_OUT1ALT	TIM1_CC2 #0	US0_CLK #3	LES_CH15 #0 DBG_SWO #1
49	PF0		TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1
50	PF1		TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1 GPIO_EM4WU3
51	PF2	LCD_SEG0	TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
52	PF3	LCD_SEG1			PRS_CH0 #1
53	PF4	LCD_SEG2			PRS_CH1 #1
54	PF5	LCD_SEG3			PRS_CH2 #1
55	IOVDD_5	Digital IO power supply 5.			
56	PE8	LCD_SEG4			PRS_CH3 #1
57	PE9	LCD_SEG5			
58	PE10	LCD_SEG6	TIM1_CC0 #1	US0_TX #0	BOOT_TX
59	PE11	LCD_SEG7	TIM1_CC1 #1	US0_RX #0	LES_ALTEX5 #0 BOOT_RX

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
US0_TX	PE10	PE7		PE13	PB7			USART0 Asynchronous Transmit.Also used as receive input in half duplex communication. USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7	PD2	PF0					USART1 clock input / output.
US1_CS	PB8	PD3	PF1					USART1 chip select input / output.
US1_RX		PD1	PD6					USART1 Asynchronous Receive. USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX		PD0	PD7					USART1 Asynchronous Transmit.Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32TG840* is shown in Table 4.3 (p. 53). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

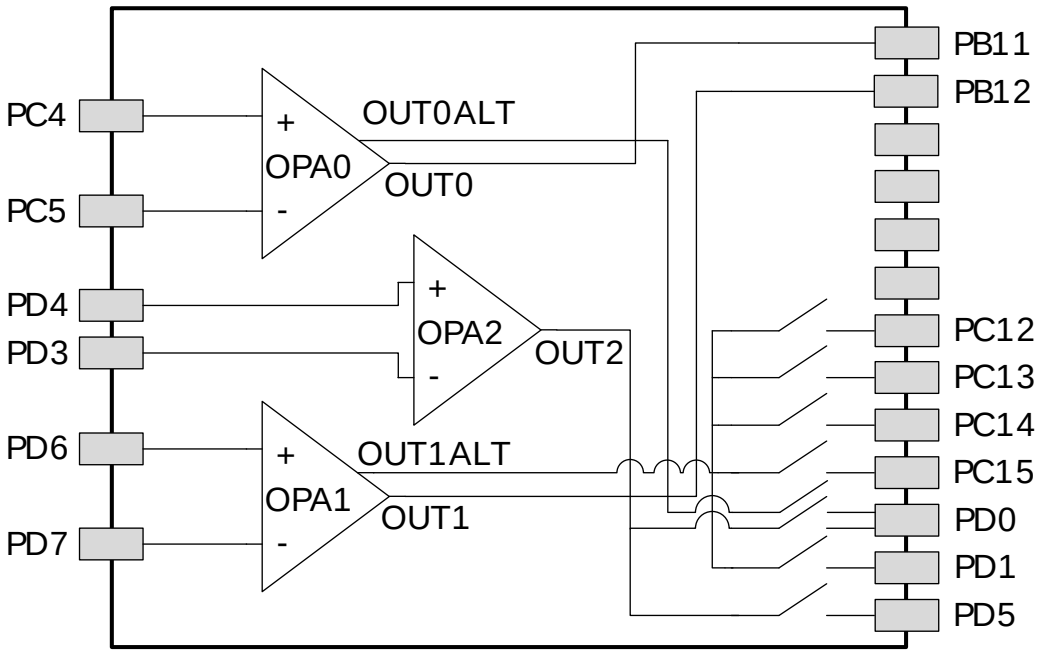
Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	PA15	PA14	PA13	PA12	-	-	-	-	-	PA6	PA5	PA4	PA3	PA2	PA1	PA0
Port B	-	PB14	PB13	PB12	PB11	-	-	PB8	PB7	PB6	PB5	PB4	PB3	-	-	-
Port C	PC15	PC14	PC13	PC12	-	-	-	-	PC7	PC6	PC5	PC4	-	-	-	-
Port D	-	-	-	-	-	-	-	PD8	PD7	PD6	PD5	PD4	PD3	PD2	PD1	PD0
Port E	PE15	PE14	PE13	PE12	PE11	PE10	PE9	PE8	PE7	PE6	PE5	PE4	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	PF5	PF4	PF3	PF2	PF1	PF0

4.4 Opamp Pinout Overview

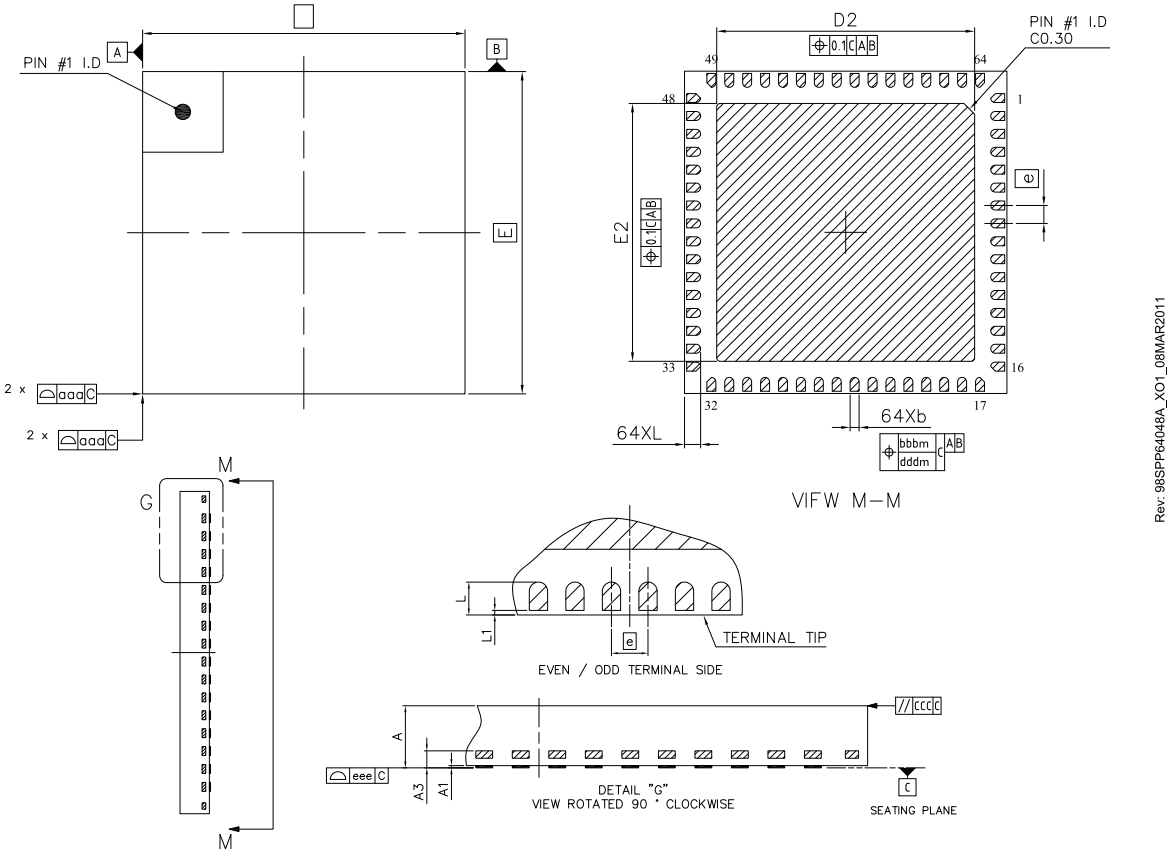
The specific opamp terminals available in *EFM32TG840* is shown in Figure 4.2 (p. 54) .

Figure 4.2. Opamp Pinout



4.5 QFN64 Package

Figure 4.3. QFN64



Note:

1. Dimensioning & tolerancing confirm to ASME Y14.5M-1994.
2. All dimensions are in millimeters. Angles are in degrees.

Figure 5.2. QFN64 PCB Solder Mask

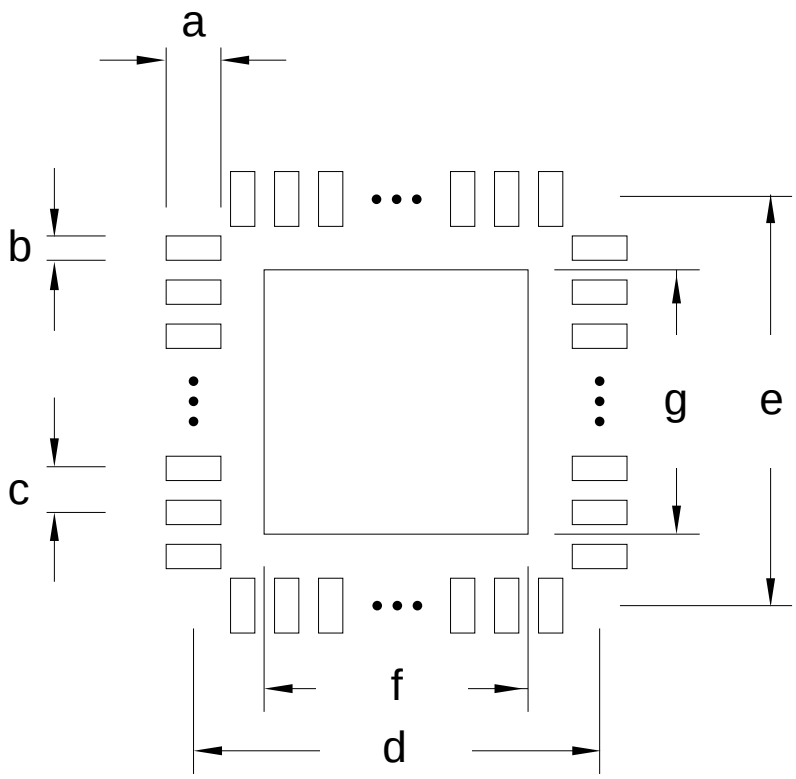


Table 5.2. QFN64 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.97	e	8.90
b	0.42	f	7.32
c	0.50	g	7.32
d	8.90	-	-

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